Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 16459-006001	Application No. 10/723,987
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Alexei A. Erchak et al.	
		Filing Date November 26, 2003	Group Art Unit

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
MC	AA	5,359,345	10/25/94	Hunter et al.			
	AB	5,631,190	05/20/97	Negley et al.			
	AC	5,724,062	03/03/98	Hunter et al.			
	AD	5,799,924	07/14/98	Krames et al.			
	AE	5,955,749	09/21/99	Joannopoulos et al.			
	AF	6,071,795	06/06/00	Cheung et al.			
	AG	6,420,242	07/16/02	Cheung et al.			
	AH	6,559,075	05/06/03	Kelly et al.			
	AI	6,410,942	06/25/02	Thibeault et al.			
	AJ	6,657,236	12/02/03	Thibeault et al.			
	AK	2003/0141507	07/31/03	Krames et al.			
	AL	5,633,527	05/27/1997	Lear			02/06/95
	AM	5,363,009	11/8/1994	Monto			08/10/92
	AN	5,073,041	12/17/1991	Rastani			11/13/90
MC	AO	5,426,657	06/20/1995	Vakhsoori			05/27/94

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
	~~AP~~	~~WO 98/14986~~	~~04/09/98~~	PCT				

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
MC	AQ	W.S. Wong et al. "Damage-free separation of GaN thin films from sapphire substrates", Appl. Phys. Lett. 72 (5), February 2, 1998, pages 599-601
MC	AR	M.K. Kelly et al. "Optical process for liftoff of Group III-nitride films", Physica Status Solidi; Rapid Research Note, November 28, 1996, 2 pages.
MC	AS	A. A. Erchak et al. "Enhanced coupling to vertical radiation using a two-dimensional photonic crystal in a semiconductor light-emitting diode", Appl. Phys. Lett. (78 (5), January 29, 2001, pages 563-565

Examiner Signature	Date Considered
	12/20/04

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute Form PTO-1449 (Modified) U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 16459-006001	Application No. 10/723,987
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))	Applicant Alexei A. Erchak et al.	
	Filing Date November 26, 2003	Group Art Unit

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
ML	AT	P.L. Gourley et al. "Optical properties of two-dimensional photonic lattices fabricated as honeycomb nanostructures in compound semiconductors", Appl. Phys. Lett. 64(6), February 7, 1994, pages 687-689
ML	AU	P.L. Gourley et al. "Optical Bloch waves in a semiconductor photonic lattice", Appl. Phys. Lett. 60 (22), June 1, 1992, pages 2714-2716
ML	AV	J.R. Wendt et al. "Nanofabrication of photonic lattice structures in GaAs/AlGaAs", J.Vac. Sci. Technol. B 11(6), November/December 1993, pages 2637-2640
ML	AW	M. Krames et al "Introduction to the Issue on High-Efficiency Light-Emitting Diodes", IEEE Journal on selected topic in quantum electronics, Vol. 8, No. 2 March/April 2002, pages 185-188
ML	AX	K. Streubel et al.. "High Brightness AlGaInP Light-Emitting Diodes", IEEE Journal on selected topic in quantum electronics, Vol. 8, No. 2, March/April 2002, pages 321-332
ML	AY	M. Okai et al. "Novel method to fabricate corrugation for a λ/4-shifted distributed feedback laser using a granting photomask", Appl. Phys. Lett. 55(5), July 31, 1989, pages 415-417
ML	AZ	T.L. Koch et al. "1.55-μ InGaAsP distributed feedback vapor phase transported buried heterostructure lasers", Appl. Phys. Lett. 47 (1), July 1, 1985, pages 12-14
ML	AAA	W.T. Tsang et al. "Semiconductor distributed feedback lasers with quantum well or superlattice grating for index or gain-coupled optical feedback", Appl. Phys. Lett. 60 (21), May 25 1992, pages 258-2582
ML	ABB	M. Zelsmann et al. "Seventy-fold enhancement of light extraction from a defectless photonic crystal made on silicon-on-insulator", Appl. Phys. Lett. 83 (13), September 29, 2003, pages 2542-2544
ML	ACC	M. Rattier et al. "Omnidirectional and compact guided light extraction from Archimedean photonic lattices", Appl. Phys. Lett. 83 (7), August 18, 2003, pages 1283-1285
ML	ADD	Y.-J. Lee et al. "A high-extraction-efficiency nanopatterned organic light-emitting diode", Appl. Phys. Lett. 82(21), May 26, 2003, pages 3779-3781
ML	AEE	I. Schnitzer et al. "30% external quantum efficiency from surface textured, thin-film light-emitting diodes", Appl. Phys. Lett. 63 (18), October 18, 1993, pages 2174-2176
ML	AFF	M. Boroditsky et al. "Light extraction from optically pumped light-emitting diode by thin-slab photonic crystals", Appl. Phys. Lett. 75 (8), August 23, 1999, pages 1036-1038
ML	AGG	L. Chen et al. "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures", Phys. Stat. Sol. (a), 188 (1), 2001, pages 135-138.
ML	AHH	I. Bulu et al. "Highly directive radiation from sources embedded inside photonic crystals", Appl. Phys. Lett. 83 (16), October 20, 2003, pages 3263-3265
ML	AII	T. N. Oder et al. "III-nitride photonic crystals", Appl. Phys. Lett. 83 (6), August 11, 2003, pages 1231-1233
ML	AJJ	M.K. Kelly et al. "Optical patterning of GaN films", Appl. Phys. Lett 68 (12), September 16, 1996, pages 1749-1751

Examiner Signature	Date Considered
ML	12/20/04

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.